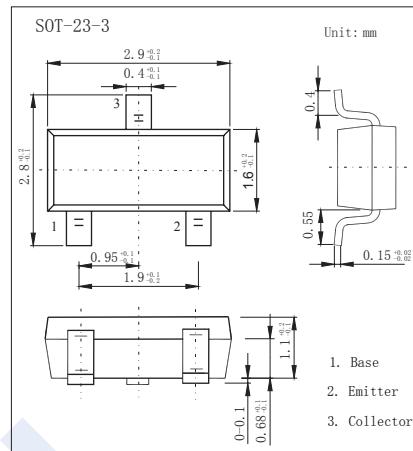


PNP Transistors

BCX71 (KCX71)

■ Features

- Low current (max. 100 mA)
- Low voltage (max. 45 V)
- Low noise.
- NPN complements: BCX70 series.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CBO}	-45	V
Collector - Emitter Voltage	V _{CEO}	-45	
Emitter - Base Voltage	V _{EBO}	-5	
Collector Current - Continuous	I _C	-100	mA
Peak Collector Current	I _{CM}	-200	
Peak Base Current	I _{BM}	-200	
Collector Power Dissipation	P _C	250	mW
Thermal Resistance Junction to Ambient (Note.1)	R _{θJA}	500	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

Note.1: Transistor mounted on an FR4 printed-circuit board.

PNP Transistors**BCX71 (KCX71)**

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CBO}	I _c = -100 μA, I _E =0	-45			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = -1 mA, I _E =0	-45			
Emitter - base breakdown voltage	V _{EBO}	I _E = -100 μ A, I _c =0	-5			
Collector-base cut-off current	I _{CBO}	V _{CB} = -45 V , I _E =0			-20	nA
		V _{CB} = -45 V , I _E =0, T _{amb} = 150°C			-20	uA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V , I _c =0			-20	nA
Collector-emitter saturation voltage	V _{CESat}	I _c =-10 mA, I _B =- 0.25mA	-60		-250	mV
		I _c =-50 mA, I _B = -1.25mA (Note.1)	-120		-550	
Base - emitter saturation voltage	V _{BESat}	I _c =-10 mA, I _B =- 0.25mA	-600		-850	
		I _c =-50 mA, I _B = -1.25mA (Note.1)	-680		-1050	
Base - emitter voltage	V _{BE}	V _{CES} = -5V, I _c = -2mA	-600	-650	-750	
		V _{CES} = -5V, I _c = -10uA		-550		
		V _{CES} = -1V, I _c = -50mA (Note.1)		-720		
DC current gain	BCX71H	V _{CES} = -5V, I _c = -10uA	30			
	BCX71J		40			
	BCX71K		100			
DC current gain	BCX71H	V _{CES} = -5V, I _c = -2mA	180		310	
	BCX71J		250		460	
	BCX71K		380		630	
DC current gain	BCX71H	V _{CES} = -1V, I _c = -50mA (Note.1)	80			
	BCX71J		100			
	BCX71K		110			
Collector capacitance	C _c	V _{CB} =-10V,I _E =I _E =0,f=1MHz		4.5		pF
Emitter capacitance	C _e	V _{EB} =-0.5 V,I _c =I _c =0,f=1MHz		11		
Noise figure	NF	I _c = -200 μA; V _{CE} = -5 V; R _s = 2 kΩ; f = 1 kHz; B = 200 Hz		2	6	dB
Transition frequency	f _T	V _{CES} = -5V, I _c = -10mA,f=100MHz	100			MHz

Note.1: Pulse test: tp ≤ 300 μs; δ ≤ 0.02.

■ Classification of h_{FE}(2)

Type	BCX71H	BCX71J	BCX71K
Range	180-310	250-460	380-630
Marking	BH*	BJ*	BK*